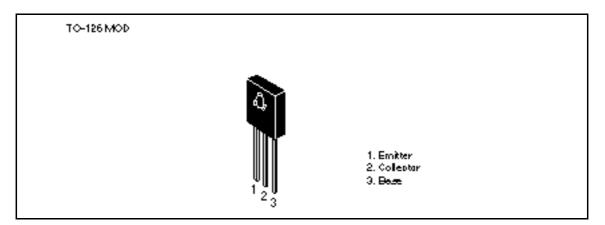
Silicon NPN Epitaxial

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#### Application

Low frequency power amplifier complementary pair with 2SB649/A

#### Outline





# **Absolute Maximum Ratings** (Ta = 25°C)

	Ratings			
Symbol	2SD669	2SD669A	Unit	
V <sub>CBO</sub>	180	180	V	
V <sub>CEO</sub>	120	160	V	
V <sub>EBO</sub>	5	5	V	
Ι <sub>c</sub>	1.5	1.5	А	
I <sub>C(peak)</sub>	3	3	А	
Pc	1	1	W	
P <sub>c</sub> * <sup>1</sup>	20	20	W	
Tj	150	150	°C	
Tstg	-55 to +150	-55 to +150	°C	
	V <sub>CBO</sub> V <sub>CEO</sub> V <sub>EBO</sub> I <sub>C</sub> I <sub>C</sub> (peak) P <sub>C</sub> P <sub>C</sub> * <sup>1</sup> Tj	Symbol 2SD669 $V_{CBO}$ 180 $V_{CEO}$ 120 $V_{EBO}$ 5 $I_c$ 1.5 $I_{C(peak)}$ 3 $P_c$ 1 $P_c^{*1}$ 20   Tj 150	Symbol 2SD669 2SD669A $V_{CBO}$ 180 180 $V_{CEO}$ 120 160 $V_{CBO}$ 5 5 $I_c$ 1.5 1.5 $I_{C(peak)}$ 3 3 $P_c$ 1 1 $P_c^{*1}$ 20 20   Tj 150 150	

Note: 1. Value at  $T_c = 25^{\circ}C$ .

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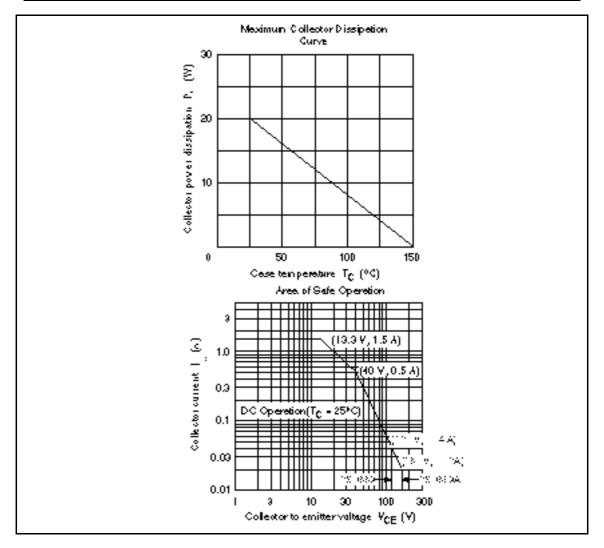
# **Electrical Characteristics** (Ta = $25^{\circ}$ C)

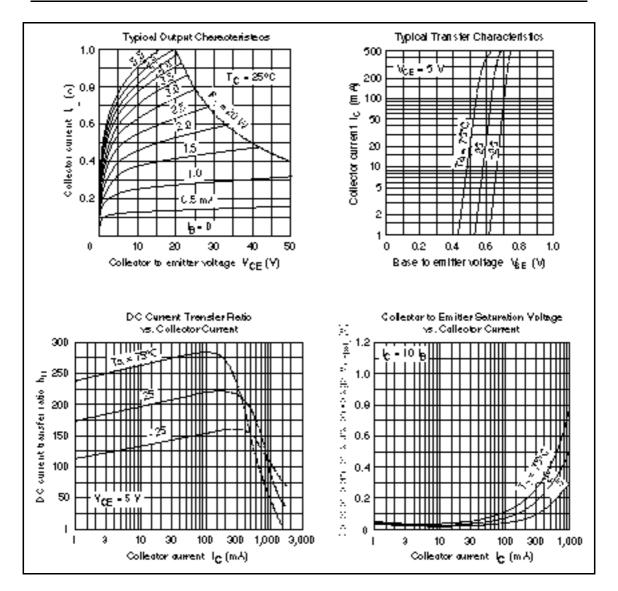
		2SD669		2SD669A					
Item	Symbol	Min	Тур	Max	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	180	—	—	180	_	—	V	$I_{c} = 1 \text{ mA}, I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(\text{BR})\text{CEO}}$	120	—	—	160	_	—	V	$I_c = 10 \text{ mA}, \text{ R}_{\text{\tiny BE}} =$
Emitter to base breakdown voltage	$V_{(\text{BR})\text{EBO}}$	5	_	_	5	_	_	V	$I_{\rm E} = 1$ mA, $I_{\rm C} = 0$
Collector cutoff current	I <sub>CBO</sub>	_	_	10	_	_	10	μA	$V_{CB} = 160 \text{ V}, I_{E} = 0$
DC current transfer ratio	$h_{\rm FE1}^{*1}$	60	_	320	60	_	200		$V_{ce} = 5 \text{ V}, \text{ I}_{c} = 150 \text{ mA}^{*2}$
	$h_{\text{FE2}}$	30	_	_	30	_	_		$V_{ce} = 5 \text{ V}, I_c = 500 \text{ mA}^{*2}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	1	_	_	1	V	$I_{c} = 500 \text{ mA},$ $I_{B} = 50 \text{ mA}^{*2}$
Base to emitter voltage	$V_{BE}$	_	_	1.5	_	_	1.5	V	$V_{ce} = 5 \text{ V}, I_c = 150 \text{ mA}^{*2}$
Gain bandwidth product	f <sub>T</sub>	_	140	_	_	140	_	MHz	$V_{ce} = 5 \text{ V}, I_c = 150 \text{ mA}^{*2}$
Collector output capacitance	Cob	—	14	_	_	14	_	pF	$V_{CB} = 10 \text{ V}, \text{ I}_{E} = 0,$ f = 1 MHz

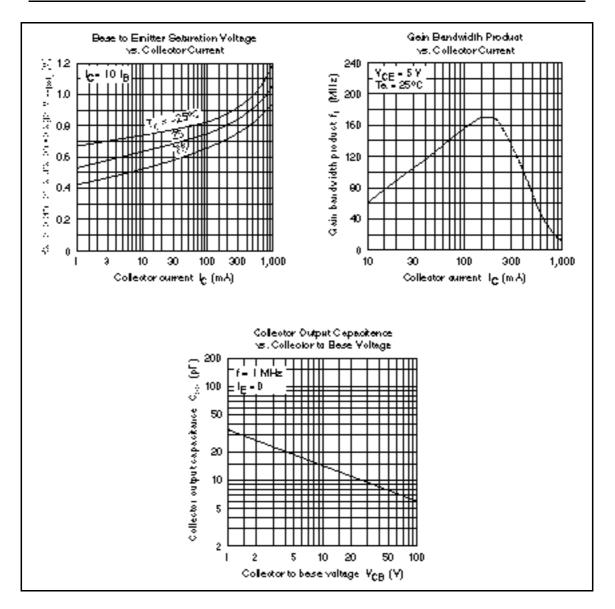
Notes: 1. The 2SD669 and 2SD669A are grouped by  $\rm h_{\rm FE1}$  as follows.

2. Pulse test.

	В	С	D
2SD669	60 to 120	100 to 200	160 to 320
2SD669A	60 to 120	100 to 200	_







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